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PATENT APPLICATION
ATTORNEY DOCKET NO. LMRX-P019/P1154

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Lee et al.
Application No. 10/623,016
Filed: 7/17/2003
Title: TREATMENT FOR CORROSION IN
SUBSTRATE PROCESSING

Examiner: DEO, Duy V. Nguyen
Group No. 1765
Confirmation No. 4601

CERTIFICATE OF FACSIMILE TRANSMISSION
I hereby certify that this correspondence is being transmitted to the U.S.
Patent Office on April 21, 2005 via facsimile transmission to fax
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Signed: /Alma Fazlic/
Alma Fazlic

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

The references listed in the attached PTO Form 1449 may be material to the patentability of the above-identified patent application. Applicants submit the list of these references in compliance with their duty of disclosure pursuant to 37 CFR §§ 1.56 and 1.97. The Examiner is requested to make these references of official record in this application. The above-identified application is a continuation-in-part of prior application U.S. Patent Application No. 10/199,190 filed on July 19, 2002, which in turn is a continuation-in-part of U.S. Patent Application No. 9/820,696 filed on March 30, 2001. This prior application is being relied upon for an earlier filing date under 35 U.S.C. § 120. Because the listed references were either cited by the PTO, or submitted to the PTO in the prior application, under 37 CFR § 1.98(d) Applicants submit that copies need not be provided.

This Information Disclosure Statement is not to be construed as a representation that a search has been made, that additional information material to the examination of this application does not exist, or that these references indeed constitute prior art.

This Information Disclosure Statement is believed to be filed before the mailing date of a first Office Action on the merits. If it is determined that fees are due, the Commissioner is hereby authorized to charge such fees to Deposit Account 50-2284 (Order No. LMRX-P019).

Respectfully submitted,

By: /Joseph Nguyen/
Joseph Nguyen
Reg. No. 37,899

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Examiner Signature		Date Considered	
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